

Photoelectrochemistry of Heterointerfaces for Solar Fuels



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What we do



Marie Curie "Arcadia" (H2020-MSCA-IF 2015)

CARIPLO « ECONOMIA CIRCOLARE: RICERCA PER UN FUTURO SOSTENIBILE»: **CO2 Enrich»** 2021-2024 (with Statale di Milano and Milano Bicocca)

Horizon Europe SOREC2 (2022-2025) https://cordis.europa.eu/project/id/101084326



Content

- Electron levels in semiconductors and some photoelectrochemistry concepts
- Case studies about charge transfer processes at modified interfaces
- Conclusions, consequences and applications

Artificial photosynthesis via photoelectrochemical cells



In a photoelectrosynthetic cell: either hydrogen or carbon dioxide reduction product could be obtained. Hydrogen is «easy», selective reduction of CO_2 is also feasible but more challenging due to several reaction pathways



Several possible reduction semireactions:

 $CO_{2} + 2H^{+} + 2e^{-} \rightarrow HCO_{2}H$ $CO_{2} + 2H^{+} + 2e^{-} \rightarrow CO + H_{2}O$ $2CO_{2} + 2H^{+} + 2e^{-} \rightarrow H_{2}C_{2}O_{4}$ $CO_{2} + 4H^{+} + 4e^{-} \rightarrow HCHO + H_{2}O$ $CO_{2} + 6H^{+} + 6e^{-} \rightarrow CH_{3}OH + H_{2}O$ $CO_{2} + 8H^{+} + 8e^{-} \rightarrow CH_{4} + 2H_{2}O$



at the (photo)cathode

- **Oxidation semireaction:**
 - $2 H_2 O \rightarrow 4 H^+ + 4 e^- + O_2$
 - at the (photo)anode



OER as a key step to solar fuels



a) Water Nucleophilic Attack (WNA)



b) Oxo-Coupling Mechanism (I2M)



c) Lattice Oxygen Evolution Reaction (LOER)





FIGURE 1 Schematic of the PEMWE cell used for the study.





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Typical n-type PEC Current/Voltage characteristic: voltage saving with respect to conventional electrolysis







$J(x) = n(x)\mu_n(x)(\nabla U(x) + \nabla \mu(x))$

- J(x) = carrier flux
- n(x)= carrier concentration
- $\mu_n(x)$ Mobility (velocity/field)
- $abla U(x) = \begin{array}{l} ext{Electric potential gradient (electric field)} \\ ext{(drift/migration)} \end{array}$

$abla \mu(x)$ Chemical potential gradient (diffusion)

Either or just one of these fields give rise to the flow of carriers which trigger photoelectrochemical reactions at the interfaces of the PEC

A more complete view of energy levels in real solids

Fig. 2.6 Energy levels of shallow and deep donors (SD, DD) and acceptors (SA, DA) in a semiconductor. Deep donor or acceptor states can also occur below or above midgap, respectively. Midgap states (RC) are often very efficient recombination centers and can be either donor- or acceptor-like in nature



Formation of Semiconductor/electrolyte Junction (Schottky model)





Principles and Applications of Semiconductor Photoelectrochemistry

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Figure 11. The spatial dependence of the charge density, the electric field, and the electric potential in the semiconductor at equilibrium. The origin of the x-axis (the distance axis) is chosen for convenience as the point where the net charge density in the semiconductor becomes zero. (a) The distance dependence of the charge density under the depletion approximation. (b) The electric field strength as a function of distance. Note that the maximum electric field strength occurs at the semiconductor/liquid interface. (c) The distance dependence of the electric potential in the semiconductor. The electric potential in the bulk of the semiconductor has been defined to be zero. Because the sign of the electric field strength is positive, the electric potential at the interface is more negative than it is in the bulk.

Semiconductor/Electrolyte interface





Figure 2.2. Double layers at the solid/liquid interface. The dashed line through the liquid indicates the variation in potential energy of a unit negative charge, as determined only by the double layer voltages, as it moves from the conduction band of the solid into the solution. The Gouy layer thickness indicated would represent a very dilute solution (Section 2.2.2).

Electrochemistry at Semiconductor and Oxidized Metal Electrodes

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J-V characteristic under illumination: n-type SC



Fig. 6.7 Band diagram of a n-type photoanode at (a) flat-band potential, (b) a potential sufficient to separate charge carriers and drive photocurrent, and (c) large reverse bias potential sufficient to saturate the photocurrent response. The corresponding hypothetical j-V curve is shown on the *right*

Photovoltage and quasi-Fermi levels



Fig. 2.20 Band diagram for a PEC cell based on an n-type semiconducting photoanode that is electrically connected to a metal counter electrode; in equilibrium in the dark (*left*) and under illumination (*right*). Illumination raises the Fermi level and decreases the band bending. Near the semiconductor/electrolyte interface, the Fermi level splits into quasi-Fermi levels for the electrons and holes

$$\varepsilon_{\mathrm{F(SC)}} = \varepsilon_{\mathrm{C}} - k T \ln\left(\frac{N_{\mathrm{C}}}{n}\right), \quad \varepsilon_{\mathrm{F(SC)}} = \varepsilon_{\mathrm{V}} + k T \ln\left(\frac{N_{\mathrm{V}}}{p}\right)$$

$${}_{n}\varepsilon_{F}^{*} = \varepsilon_{C} - k T \ln\left(\frac{N_{C}}{n^{*}}\right) = \varepsilon_{F(SC)} + k T \ln\left(\frac{n + \Delta n^{*}}{n}\right)$$
$${}_{p}\varepsilon_{F}^{*} = \varepsilon_{V} + k T \ln\left(\frac{N_{V}}{p^{*}}\right) = \varepsilon_{F(SC)} - k T \ln\left(\frac{p + \Delta p^{*}}{p}\right)$$

SEMICONDUCTORS for PEC DEVICE





Fig. 3 Energy level diagrams for a semiconductor-metal photoelectrolysis cell: (a) no contact, (b) equilibrium in the dark, (c) high intensity irradiation, (d) high intensity irradiation with anodic bias

Some tandem PEC configurations



photonics

PUBLISHED ONLINE: 11 NOVEMBER 2012 | DOI: 10.1038/NPHOTON.2012.26

Highly efficient water splitting by a dual-absorber tandem cell

Jeremie Brillet¹, Jun-Ho Yum¹, Maurin Cornuz¹, Takashi Hisatomi¹, Renata Solarska², Jan Augustynski², Michael Graetzel¹ and Kevin Sivula¹*

"Water splitters fabricated using triple-junction amorphous silicon1,2 or III–V3 semiconductors have demonstrated reasonable efficiencies, but at high cost and high device complexity"

Fig. 2.25 Examples of possible PEC configurations under illumination. *Top row*: Standard singlesemiconductor devices based on a photoanode (a) or photocathode (b) with a metal counter electrode. *Middle row*: Monolithic devices based on a photoanode (c) or photocathode (d) biased with an integrated p-n junction. *Bottom row*: p-n junction photoelectrochemical device (e), and an n-n heterojunction PEC device based on a photoanode deposited on top of a second n-type semiconductor that "boosts" the energy of the electrons (f)



Fig. 1.2 Theoretical maximum solar-to-hydrogen (STH) conversion efficiency (*left axis*) and photocurrent (*right axis*) as a function of material band gap.

Nanostructured Materials

GOOD PROPERTIES

- Active Surface
- low T, wet routes available
- Diffusion Length



Sol-gel TiO_2

Drawbacks

Defects/SS

•Traps

Conduction band $-E_{SD}$ $-E_{DD}$ $-E_{DA}$ E_{RC} $-E_{DD}$ $-E_{DA}$ E_{V} Valence band

Tuning the surface properties with "catalytic" layers

Composite photoanodes n-SC/WOC CB e $O_{2} + 4 H^{+}$ $2 H_2 O$ VB WOC = Water Oxidation Catalyst n-type SC to the counter electrode (cathode) through the circuit

Catalytic layers as SCs overcoatings





fast electron/hole recombination



FIG. 11. The band structures for pure hematite (upper) and 8% Pd-doped (lower) are plotted across high-symmetry directions in the Brillouin zone. Here, we use the conventions K = (1/3, 1/3, 0), M = (1/2, 0, 0), $\Gamma = (0, 0, 0), A = (0, 0, 1/2), H = (1/3, 1/3, 1/2), and L = (1/2, 0, 1/2).$ The zero of energy in each case is the energy of the highest occupied band.

low hole mobility (L_D 2-4 nm) (-+)low electronic conductivity d high number of traps nanostructuring doping slow hole/interfacial transfer kinetics (0.001 - 1 ms timescale) surface modification 3

C

Rough Surface

Flat Surface



Amorphous Fe(III) oxide as a water oxidation catalyst



Cite this: Phys. Chem. Chem. Phys., 2013,

15, 13083

devices functionalized with earth-abundant oxygen evolving catalysts†

Vito Cristino,^a Serena Berardi,^b Stefano Caramori,^{*a} Roberto Argazzi,^b Stefano Carli,^a Laura Meda,^c Alessandra Tacca^c and Carlo Alberto Bignozzi^{*a}





Fig. 7 J–V curves recorded under AM 1.5 G illumination in 0.5 M Na₂CO₃ (pH 11.2). The 3J cell (either modified with Fe-OEC or unmodified) is used as the photoanode in a three electrodes cell. Inset: photoaction spectrum of Fe-OEC-3J in a three electrodes cell, recorded in 0.5 M Na₂CO₃ (pH 11.2) at 0 V vs. SCE.



1- HYDROTHERMAL SYNTHESIS OF HEMATITE THIN FILM



CHEMPHYSCHEM ARTICLES ChemPubSoc Europe

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Hematite Photoanodes Modified with an Fe^{III} Water Oxidation Catalyst

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2- SILAR DEPOSITION OF Fe-OEC



x 10 times

200°C x 20'

Photoelectrochemical behavior of Fe-OEC modified interface



Figure 3. *J–V* curves under continuous and shuttered illumination (AM 1.5 G) of Fe-OEC-modified hematite (grey line) compared to the unmodified hematite (black line) in 0.5 м sodium borate buffer (pH 11.5).







Figure 5. Open-circuit photovoltage decays of: A) unmodified hematite (black line) and Fe-OEC-modified hematite (same electrode after functionalization) (grey line) in 0.5 m sodium borate buffer (pH 11.5); B) unmodified hematite in the absence and in the presence of 0.1 m K₄[Fe(CN)₆] in sodium borate buffer (pH 11.5). For the sake of clarity, in all cases ΔV_{photo} was normalized to the same value.



Figure 6. Complex plane plot (0.3 V vs. SCE) of the same hematite electrode before (black squares) and after (grey circles) functionalization with Fe-OEC under AM 1.5 G illumination in 0.5 m sodium borate buffer (pH 11.5). The data are fitted (solid line) with the model reported in Scheme 2.



Figure 9. Capacitance of the semiconductor/electrolyte interface under AM 1.5 G illumination (100 mWcm⁻²) of the same hematite electrode before (black squares) and after (grey circles) surface modification with Fe-OEC measured in 0.5 м sodium borate buffer (pH 11.5). The grey bar indicates the thermodynamic potential for oxygen evolution.

«the interfacial behavior is dominated by hole trapping in surface states, which are believed to be the intermediates responsible for the OER. The considerable increase in the surface trap capacitance in the presence of FeOEC indicates a favorable transfer of holes to the catalyst, which, being an amorphous hydrated oxide, easily undergoes PCET allowing the long lived storage of oxidizing equialvents in reactive states exposed to the electrolyte »

Ti(IV) modified hematite interfaces



Serena Berardi, Jagadesh Kopula Kesavan, Lucia Amidani, Elia Marek Meloni, Marcello Marelli, Federico Boscherini, Stefano Caramori, and Luca Pasquini*



Research Article

Figure 6. TEM micrographs of MPH_5Ti, related ESI Fe and Ti maps, and the combined map.





Energy Environ. Sci., 2015,8, 3242-3254



Figure 2. Ti K edge normalized XANES spectra of Ti-modified MPH compared to pseudobrookite, anatase, brookite, rutile, and ilmenite reference spectra.

Transient Optical Absorption in semiconductors: a simplified view



Transient Spectroscopy of Ti-modified hematite





Ilmenite overlayer eliminates electron traps and unpins hematite Fermi level from traps, allowing for a stronger depletion layer to form. FeOEC improves Interfacial charge transfer





Capitalizing Hematite Photoanodes for Biomass Oxidation

Deng *et al.* hydrothermal synthesis to produce nanostructured thin films of hematite



- Variation of time, temperature and pressure
- Additives in the autoclave solution
- Seedlayers/underlayers

Can affect the **thickness** and the **morphological growth** of hematite film



J. Deng et al., *J. Appl. Phys.*, 112, 084312, 2012

D.K. Bora, Materials Science in Semiconductor Processing, 31, 2015, 728–738

Hematite photoanodes for Biomass oxidation: from HMF to FDCA



Kawde, A. et al., *Catalysts* 2021, 11, 969

CO2UDOR

J-V curves with and without TEMPO





Electrochemical Impedance Spectroscopy of Hematite with CoPi catalyst



Additional mesh to account for charge transfer through the CoPi layer.

Holes trapped in Hema's SS are transferred to the CoPi layer, which subsequently transfers them to the electrolyte

Rrec,cat = recombination resistance through CoPi Ccat = capacitance associated to CoPi



$$\begin{split} R_{tot} &= R_s + R_{ct} + R_{rec} + R_{rec,cat} \\ R_s &= R_{series} \\ R_{ct} &= R_{charge\ transfer} \\ R_{rec} &= R_{recombination} \\ R_{rec,cat} &= R_{recombination\ from\ cat} \\ C_{sc} &= C_{space\ charge} \\ C_{ss} &= C_{surface-states} \\ C_{cat} &= C_{catalyst} \end{split}$$

Hema with CoPi: Borate buffer vs borate buffer+TEMPO



Conversion of HMF into FDCA

Because of the competition with OER, a full conversion of HMF to FDCA is not reached.

The presence of CoPi onto the hematite surface seems to increase the selectivity towards FDCA.



Electrode	Time of the exp (h)	Total charge passed (C)	HMF consumed (%)	Conv HMF exp in DFF (%)	Conv HMF exp in FFCA (%)	Conv HMF exp in FDCA (%)	Faradaic efficiency for FFCA+FDCA (FE%)
Hema+CoPi	18	117	100	0	31	73	70
Hema+CoFeO x	18	110	100	0	51	56	75
Hematite	19	83	100	0	57	43	89

Sol-Gel Routes to transparent WO₃ electrodes





C. Santato, M. Odziemkowski, M. Ulmann and J. Augustynski, JACS 2001, 123, 10639-10640
C. Santato, M. Ulmann and J. Augustynski, J.Phys.Chem.B, 2001, 105, 936-940
R. Solarska, B. D. Alexander and J. Augustynski, J.Solid State Electrochem. 2004, 8, 748-756
L. Meda, G. Tozzola, A. Tacca, G. L. Marra, S. Caramori, V. Cristino and C. A. Bignozzi, Sol. Energy Mater. and Sol. Cells 2010, 94, 788-796



Citation: Mohamedkhair, A.K.; Drmosh, Q.A.; Qamar, M.; Yamani, Z.H. Tuning Structural Properties of WO3 Thin Films for Photoelectrocatalytic Water Oxidation. *Catalysts* 2021, *11*, 381. https://doi.org/10.3390(catal1100088)

Contents tots available at ScienceOffect
Applied Catalysis B: Environmental

ental 204 (2017) 273-283

nm

Eg = 2.61 eV

Photoelectrochemical mineralization of emerging contaminants at porous WO3 interfaces

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Density of sate (electro

n-n WO₃–BiVO₄ heterojunctions

Electrodeposition conditions:

inally proposed by Seabold.³¹ Briefly, 10 mM VOSO₄ in millipore water is acidified by addition of HNO₃ up to pH 0.5 followed by the addition of 10 mM $Bi(NO_3)_3$. Further HNO₃ is added until $Bi(NO_3)_3$ is completely dissolved. After this point the pH is quickly increased to 4.5 by using 2 M CH₃COONa. This solution is rapidly used (to avoid excessive hydrolysis and precipitation of Bi³⁺ compounds) for two electrode potentiostatic electrodeposition by applying 210 mV between FTO/WO₃ and a platinum foil for 600 s at room temperature.





WO₃-BiVO₄



BiVO₄ H₂O/H₂ WO₂ Monoclinic (scheelite) ٩ V 3d 4 H₂O/O₂ 2 VIS .6 eV 2.4 e\ absorption 2 Bi 6s O 2p

I. Grigioni et al. J. Phys. Chem. C 2015, 119, 36, 20792–20800

Park, Y.; McDonald, K. J.; Choi, K.-S. Progress in Bismuth Vanadate Photoanodes for Use in Solar Water Oxidation Chem. Soc. Rev. 2013, 42, 2321-2337

IACS

Efficient and Stable Photo-Oxidation of Water by a Bismuth Vanadate Photoanode Coupled with an Iron Oxyhydroxide Oxygen Evolution Catalyst Jason A. Seabold and Kyoung-Shin Choi®

dx.doi.org/10.1021/ia209001d | J. Am. Chem.Soc. 2012, 134, 2186-2192

Photochemical & **Photobiological Sciences**

Photoelectrocatalytic degradation of emerging () Check for update Cite this: Pho

contaminants at WO3/BiVO4 photoanodes in aqueous solution†

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Performances of n-n WO₃–BiVO₄ heterojunctions



Fig. 5 (A) J/V curves of WO₃/BiVO₄ compared to those of WO₃ under 0.1 W cm⁻² AM 1.5 G illumination. (B) Comparative IPCE spectra taken at 1.5 V vs. SCE. In this case front side (from the electrolyte) illumination was adopted; 0.5 M Na₂SO₄ at pH 7.





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Research Article

www.acsami.org

Cobalt Hexacyanoferrate on BiVO₄ Photoanodes for Robust Water Splitting

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Unraveling Charge Transfer in CoFe Prussian Blue Modified $BiVO_4$ Photoanodes

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RESEARCH ARTICLE

(a)

(b)

(C)

(e)



Charge Separation Efficiency in WO₃/BiVO₄ Photoanodes with CoFe Prussian Blue Catalyst Studied by Wavelength-Dependent Intensity-Modulated Photocurrent Spectroscopy

Pierpaolo Vecchi, Alberto Piccioni, Raffaello Mazzaro,* Michele Mazzanti, Vito Cristino, Stefano Caramori, and Luca Pasquini*



 WO_3 WO₃/BiVO₄ WO₃/BiVO₄/CoFe-BP



Photon to Electron Conversion Efficiency

1



- Given sufficient bias, all photoanodes reach the same photoconversion efficiency, consistent with the limiting photocurrent density.
- It is the same maximum conversion recorded with a fast scanveger (SO_3^{2-}).
- The limiting value is thus set by the carrier transport efficiency

$$PCE = \phi_{e/h} \times \eta_{transport} \times \eta_{interface} \times LHE$$

Transient Absorption



Fitting model of BiVO₄ photohole decay : sum of power law + KWW function



Transient Amplitudes vs photocurrent (460 nm)



Hole Lifetime (500 nm)



Photohole lifetime is larger when CoFePB is present. Transfer from $BiVO_4$ to the catalytic PB layer is not faster compared to the transfer process at the $BiVO_4$ /phosphate interface

A look at the interfacial capacitance of BiVO₄



Conclusions

KWW amplitudes of photoholes are apparently related to photocurrent generation, i.e. they represent the fraction of holes that can be eventually injected in the electrolyte, escaping fast power law recombination.

The CoFe-BP catalyst allows a larger population of holes in BiVO₄ to survive recombination, i.e. KWW amplitudes grow faster at lower voltages compared to the unmodified junction

EIS investigation suggests that upon CoFe PB elimination of electron traps occurs, allowing the unpinning of the Fermi level of $BiVO_4$. Thus for equivalent overvoltages a deeper depletion layer achieves a better electron hole separation (hence better collection efficiency at lower voltage). The increase in photohole amplitude and lifetime is consistent with such interpretation

General Remarks

Photoelectrochemical Cells are the most direct pathway to storage of solar energy into chemical energy, ot to exploit solar power for environmental remediation processes

Some materials, particularly metal oxides, are cheap, easy to produce and display stability under photoanodic conditions in water based electrolytes. They enjoy suitable energetics to drive demanding electrochemical reactions and to harvest a sizable portion of the solar spectrum.

The thermodynamic limit for the STH of many semiconductors is still far from being achieved. Fundamental research is still needed to understand the optimization of the interfaces, minimize recombinative losses, improve the light management, but results and progresses are being made.